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BCW29,BCW30 PNP General Purpose Transistors

SOT-23 Plastic-Encapsulate Transistors

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客户确认：

公司签章：

部门	工程部	品保部	采购部
签名			
日期			

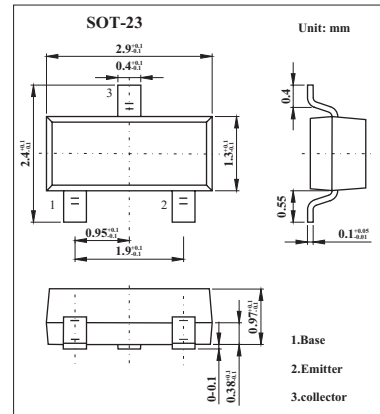


SOT-23 Plastic-Encapsulate Transistors

BCW29,BCW30 PNP General Purpose Transistors

■ Features

- Low current (max. 100 mA).
- Low voltage (max. 32 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-32	V
Collector-emitter voltage	V _{CEO}	-32	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-100	mA
Peak collector current	I _{CM}	-200	mA
Peak base current	I _{BM}	-200	mA
Total power dissipation	P _{tot}	250	mW
Storage temperature	T _{stg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	R _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient *	R _{th j-a}	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

BCW29,BCW30

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	ICBO	IE = 0; VCB = -32 V			-100	nA
	ICBO	IE = 0; VCB = -32 V; Tj = 100 °C			-10	μA
Emitter cutoff current	IEBO	IC = 0; VEB = -5 V			-100	nA
DC current gain	hFE	IC = -2 mA; VCE = -5 V	120		260	
			215		500	
Collector-emitter saturation voltage	VCE(sat)	IC = -10 mA; IB = -0.5 mA		-80		mV
		IC = -50 mA; IB = -2.5 mA		-150		mV
Base to emitter saturation voltage	VBE(sat)	IC = -10 mA; IB = -0.5 mA		-720		mV
		IC = -50 mA; IB = -2.5 mA		-810		mV
Base to emitter voltage	VBE	IC = -2 mA; VCE = -5 V	-600		-750	mV
Collector capacitance	CC	IE = ie = 0; VCB = -10 V; f = 1 MHz		4.5		pF
Transition frequency	fT	IC = -10 mA; VCE = -5 V; f = 100 MHz	100			MHz
Noise figure	NF	IC = -200 μA; VCE = -5 V; RS = 2 kΩ; f = 1 kHz; B = 200 Hz			10	dB

■ hFE Classification

TYPE	BCW29	BCW30
Marking	C1	C2